

HCF4053B

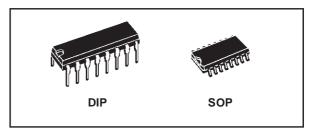
TRIPLE 2-CHANNEL ANALOG MULTIPLEXER/DEMULTIPLEXER

- LOW "ON" RESISTANCE : 125Ω (Typ.) OVER 15V p.p SIGNAL-INPUT RANGE FOR V_{DD} - V_{EE} = 15V
- HIGH "OFF" RESISTANCE : CHANNEL LEAKAGE ± 100pA (Typ.) at V_{DD} - V_{EE} = 18V
- BINARY ADDRESS DECODING ON CHIP
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. at $f_{IS} = 1$ KHz, $V_{IS} = 5 V_{pp}$, $V_{DD} - V_{SS} \ge 10$ V, RL = 10K Ω
- VERY LOW QUIESCENT POWER DISSIPATION UNDER ALL DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS : 0.2 μW (Typ.) at V_{DD} - V_{SS} = V_{DD} - V_{EE} =10V
- MATCHED SWITCH CHARACTERISTICS : $R_{ON} = 5\Omega$ (Typ.) FOR V_{DD} - V_{EE} = 15V
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS : DIGITAL 3 to 20, ANALOG TO 20V p.p.
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT $I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

The HCF4053B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor

PIN CONNECTION



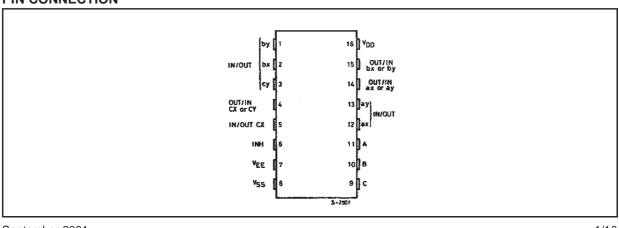
ORDER CODES

PACKAGE	TUBE	T & R
DIP	HCF4053BEY	
SOP	HCF4053BM1	HCF4053M013TR

technology available in DIP and SOP packages.

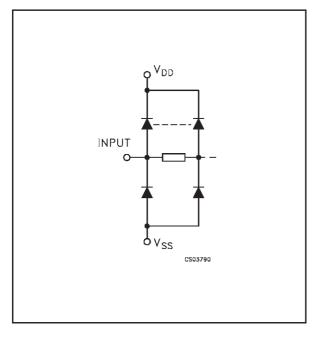
The HCF4053B analog multiplexer/demultiplexer is a digitally controlled analog switch having low ON impedance and very low OFF leakage current. This multiplexer circuit dissipate extremely low quiescent power over the full V_{DD} - V_{SS} and V_{DD} - V_{EE} supply voltage range, independent of the logic state of the control signals.

When a logic "1" is present at the inhibit input terminal all channel are off. This device is a triple 2-channel multiplexer having three separate digital control inputs, A, B, and C, and an inhibit input. Each control input selects one of a pair of channels which are connected in a single pole double-throw configuration.



September 2001

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
11, 10, 9	A, B, C	Binary Control Inputs
6	INH	Inhibit Inputs
12, 13, 2, 1, 5, 3	IN/OUT	ax,ay,bx,by,cx,cy Input/ Output
14	OUT/IN	ax or ay
15	OUT/IN	bx or by
4	OUT/IN	cx or cy
7	V_{EE}	Supply Voltage
8	V _{SS}	Negative Supply Voltage
16	V _{DD}	Positive Supply Voltage

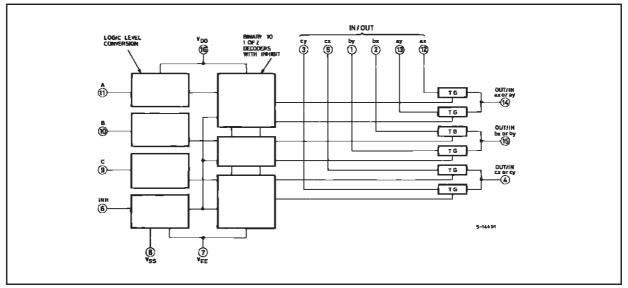
TRUTH TABLE

INHIBIT	C or B or A	
0	0	ax or bx or cx
0	1	ay or by or cy
1	Х	NONE

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X : Don't Care

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
VI	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
l _l	DC Input Current	± 10	mA
PD	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	3 to 20	V
VI	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C



HCF4053B

DC SPECIFICATIONS

		Т	est Coi	ndition					Value				
Symbol	Parameter	V _{IS}	V _{EE}	v _{ss}		т	T _A = 25°C			o 85°C	-55 to 125°C		Unit
		(V)	(V)	(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Device				5		0.04	5		150		150	
	Current (all				10		0.04	10		300		300	μA
	switches ON or all switches OFF)				15		0.04	20		600		600	μΛ
					20		0.08	100		3000		3000	
SWITCH													-
R _{ON}	Resistance	$0 \leq V_{ } \leq$			5		470	1050		1200		1200	
		V _{DD}	0	0	10		180	400		520		520	Ω
		-00			15		125	280		360		360	
Δ_{ON}	Resistance Δ_{RON}	0 <u>≤</u> V ₁ ≤			5		10						
	(between any 2 of	V _{DD}	0	0	10		10						Ω
	4 switches)				15		5						
OFF*	Channel Leakage Current (All Channel OFF) (COMMON O/I)		0	0	18		±0.1	100		1000		1000	nA
OFF*	Channel Leakage Current (Any Channel OFF)		0	0	18		±0.1	100		1000		1000	nA
CI	Input Capacitance						5						
Co	Output Capacitance		-5	-5	5		9						pF
C _{IO}	Feed through	1					0.2						1
CONTRO	DL (Address or Inhi	bit)								1		1	
V _{IL}	Input Low Voltage		Vee -	= V _{SS}	5			1.5		1.5		1.5	
				1KΩ	10			3		3		3	V
		= VDD thru		/ _{SS}	15			4		4		4	
V _{IH}	Input High Voltage	1KΩ	I _{IS} <	2μΑ	5	3.5			3.5		3.5		
				I OFF	10	7			7		7		V
			chan	nels)	15	11			11		11		
I _{IH,} I _{IL}	Input Leakage Current	VI	= 0/18\	/	18		±10 ⁻³	±0.1		±1		±1	μΑ
CI	Input Capacitance						5	7.5					pF

* Determined by minimum feasible leakage measurement for automating testing.

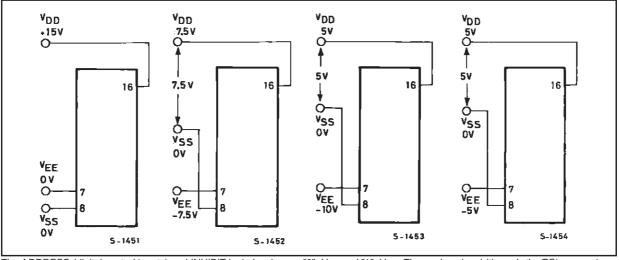
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_{L} = 50pF$, all input square wave rise and fall time = 20 ns)

				Test Co	ondition				Value		Unit
Parameter	V _{EE} (V)	R L (ΚΩ)	f _l (KHz)	V _I (∀)	V _{SS} (V)	V _{DD} (V)		Min.	Тур.	Max.	
Propagation Delay				V _{DD}		5			30	60	
Time (signal input to		200				10	1		15	30	ns
output)				╷┙└		15	1		11	20	1
Frequency Response Channel "ON" (sine	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		25		MHz
wave input) at 20 log V _O /V _I = - 3dB	55			5()			V _O at any channel		60		IVII 12
Feed through (all channels OFF) at	= V _{SS}	1		F(*)		10	V _O at Common OUT/IN		10		MHz
$20 \log V_O/V_I = -40 dB$	- v _{SS}			5(*)		10	V _O at any channel		8		
Frequency Signal Crosstalk at	= V _{SS}	1		E(*)		10	Between any 2 Sections (IN pin 2, OUT pin 14)		2.5		MHz
$20 \log V_0/V_1 = -40 dB$	- V _{SS}			5(*)		10	Between any 2 Sections (IN pin 15, OUT pin 14)		6		
				2(*)		5			0.3		
Sine Wave Distortion f _{IS} = 1KHz Sine Wave	$= V_{SS}$	10	1	3(*)		10]		0.2		%
				5(*)		15]		0.12		1
CONTROL (Address	or Inhi bi	t)									
Propagation Delay:	0				0	5			360	720	
Address to Signal	0				0	10]		160	320	ns
OUT (Channels ON or OFF)	0				0	15]		120	240	115
	-5				0	5			225	450	
Propagation Delay:	0				0	5			360	720	
Inhibit to Signal OUT	0	1			0	10]		160	320	ns
(Channel turning ON)	0				0	15]		120	240	115
	-10				0	5			200	400	
Propagation Delay:	0					5			200	450	
Inhibit to Signal OUT	0	10				10]		90	210	
(Channel turning OFF)	0					15]		70	160	ns
	-10					5]		130	300	
Address or Inhibit to Signal Crosstalk	0	10 ⁽¹⁾			0	10	$V_{C} = V_{DD} - V_{SS}$ (square wave)		65		mV peak

(1) Both ends of channel. * Peak to Peak voltage symmetrical about (V_{DD} - V_{EE}) /2

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TYPICAL BIAS VOLTAGES



The ADDRESS (digital-control inputs) and INHIBIT logic levels are : "0"=V_{SS} and "1"=V_{DD}. The analog signal (through the TG) may swing from V_{EE} to V_{DD}

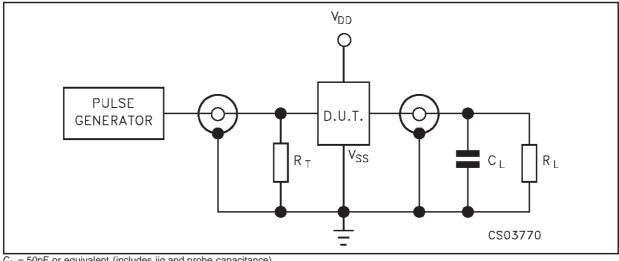
SPECIAL CONSIDERATIONS

Control of analog signals up to 20V peak to peak can be achieved by digital signal amplitudes of 4.5 to 20V (if $V_{DD} - V_{SS} = 3V$, a $V_{DD} - V_{EE}$ of up to 13V can be controlled; for $V_{DD} - V_{EE}$ level differences above 13V, a $V_{DD} - V_{SS}$ of at least 4.5V is required. For example, if $V_{DD} = +5$, $V_{SS} = 0$, and $V_{DD} = -12.5$, and $V_{DD} = -12.5$, and $V_{DD} = -12.5$. V_{EE} = -13.5, analog signals from -13.5V to 4.5V can be controlled by digital inputs of 0 to 4.5V. In

certain applications, the external load resistor current may include both V_{DD} and signal-line components. To avoid drawing V_{DD} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0,8V (calculated from RON values shown in DC SPECIFICATIONS). No V_{DD} current will flow through ${\sf R}_{\sf L}$ if the switch current flows into leads 4, 14 and $\overline{15}$.

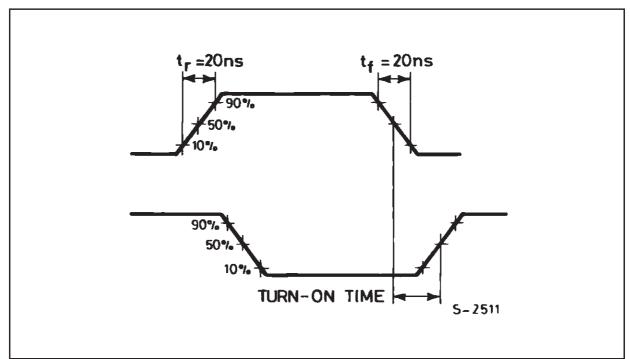
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TEST CIRCUIT



 $C_L = 50$ pF or equivalent (includes jig and probe capacitance)

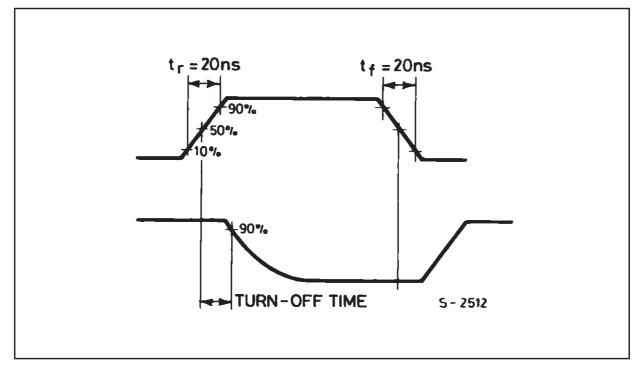
 $R_L = 200 K\Omega$ $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)



WAVEFORM 1 : CHANNEL BEING TURNED ON ($R_L = 1K\Omega$, f=1MHz; 50% duty cycle)

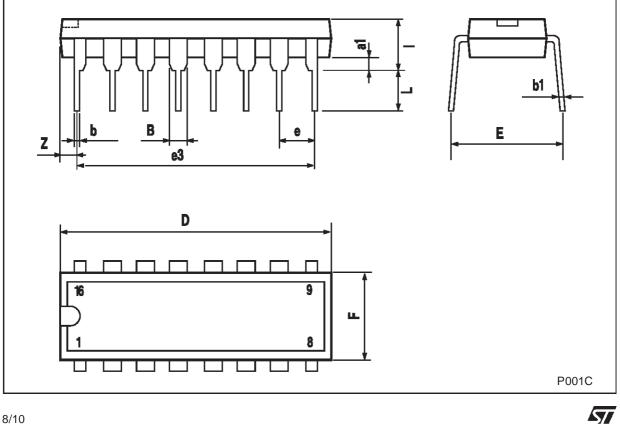
WAVEFORM 2 : CHANNEL BEING TURNED OFF ($R_L = 1K\Omega$, f=1MHz; 50% duty cycle)

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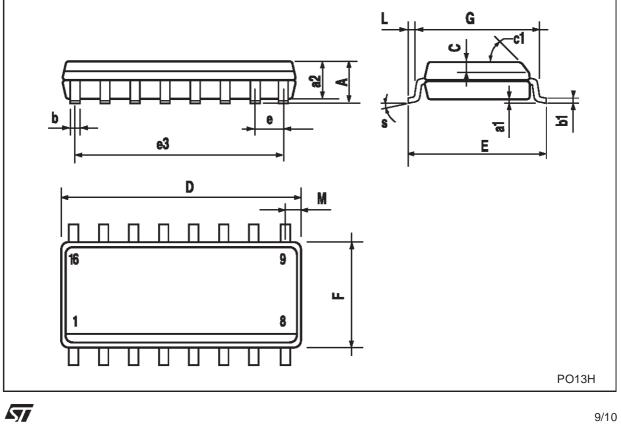
			P-16 (0.25) №			
DIM.		mm.			inch	
DIW.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z		1	1.27			0.050



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DIM.		mm.		inch					
DIIVI.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.			
А			1.75			0.068			
a1	0.1		0.2	0.003		0.007			
a2			1.65			0.064			
b	0.35		0.46	0.013		0.018			
b1	0.19		0.25	0.007		0.010			
С		0.5			0.019				
c1		•	45°	(typ.)		•			
D	9.8		10	0.385		0.393			
E	5.8		6.2	0.228		0.244			
е		1.27			0.050				
e3		8.89			0.350				
F	3.8		4.0	0.149		0.157			
G	4.6		5.3	0.181		0.208			
L	0.5		1.27	0.019		0.050			
М			0.62			0.024			





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